

L Number	Hits	Search Text	DB	Time stamp
1	807	438/167,172,571,573,582.ccls.	USPAT; US-PGPUB	2003/07/21 11:46
2	677	438/167,172,571,573,582.ccls. and @ad<20000928	USPAT; US-PGPUB	2003/07/21 12:39
3	34	(438/167,172,571,573,582.ccls. and @ad<20000928) and titanium and (compound near3 semiconductor)	USPAT; US-PGPUB	2003/07/21 12:39
4	769	257/745,755,757,769.ccls.	USPAT; US-PGPUB	2003/07/21 11:46
5	38	257/745,755,757,769.ccls. and titanium and (compound near3 semiconductor)	USPAT; US-PGPUB	2003/07/21 11:46
6	35	(257/745,755,757,769.ccls. and titanium and (compound near3 semiconductor)) not ((438/167,172,571,573,582.ccls. and @ad<20000928) and titanium and (compound near3 semiconductor))	USPAT; US-PGPUB	2003/07/21 12:37
7	55	(richard with burton) or (kyushik with hong) or (philip with canfield)	USPAT; US-PGPUB	2003/07/21 12:42
8	35	((richard with burton) or (kyushik with hong) or (philip with canfield)) and @ad<=20000928	USPAT; US-PGPUB	2003/07/21 12:40
9	1	((richard with burton) or (kyushik with hong) or (philip with canfield)) and @ad<=20000928) and titanium and (compound near3 semiconductor)	USPAT; US-PGPUB	2003/07/21 12:39
10	34	((richard with burton) or (kyushik with hong) or (philip with canfield)) and @ad<=20000928) not (((richard with burton) or (kyushik with hong) or (philip with canfield)) and @ad<=20000928) and titanium and (compound near3 semiconductor))	USPAT; US-PGPUB	2003/07/21 12:40
11	16	(richard with burton) or (kyushik with hong) or (philip with canfield)	EPO; JPO; DERWENT; IBM TDB	2003/07/21 12:42

L Number	Hits	Search Text	DB	Time stamp
1	0	((nickel with (Cr or Ti or Si)) and (ohmic adj contact) and @ad<=20000928) and (compound with semiconductor) and (nitride with liner)	USPAT; US-PGPUB	2003/07/21 17:18
2	2	(ohmic adj contact) and @ad<=20000928 and (compound with semiconductor) and (nitride with liner)	USPAT; US-PGPUB	2003/07/21 17:23
3	8	(ohmic adj contact) and @ad<=20000928 and (compound with semiconductor) and (nitride with spacer)	USPAT; US-PGPUB	2003/07/21 17:22
4	0	(ohmic adj contact) and (compound with semiconductor) and (nitride with spacer)	EPO; JPO; DERWENT; IBM_TDB	2003/07/21 17:22
5	33	(ohmic adj contact) and @ad<=20000928 and (nitride with liner)	USPAT; US-PGPUB	2003/07/21 17:23

spent 1.5 days

US-PAT-NO: 6281526

DOCUMENT-IDENTIFIER: US 6281526 B1

TITLE: Nitride compound light emitting
device and method for
fabricating same

----- KWIC -----

Detailed Description Text - DETX (16):

It was found by the inventors' experiments that good results were obtained when any one of nickel (Ni), silver (Ag), titanium (Ti), aluminum (Al) and platinum (Pt), in addition to gold, was used as the host metal.

Claims Text - CLTX (3):

a first metal layer deposited on said contact region of said n-type In.sub.x Al.sub.y Ga.sub.1-x-y N layer of said stacked structure, said first metal layer containing as a major component thereof at least one element selected from the group consisting of gold (Au), nickel (Ni), silver (Ag), titanium (Ti), aluminum (Al) and platinum (Pt), and said first metal layer additionally containing at least one element component selected from the group consisting of Group IV and VI elements,

US-PAT-NO: 6169297

DOCUMENT-IDENTIFIER: US 6169297 B1

TITLE: Metal thin film with ohmic contact
for light emit diodes

----- KWIC -----

Brief Summary Text - BSTX (16):

A metal thin film with a nickel (Ni) ohmic contact may be formed as several models, such as Ni/Au, Ni/Cr/Au and Ni/Ni/Au films, even when the semiconductor layer has a low doping concentration. However, such models have a high specific contact resistance ranged from about 1×10^{-2} ohm-cm to about 8×10^{-2} ohm-cm. In addition, the thermal property of such models is regrettably reduced due to a diffusion of nickel, thus forming a poor surface morphology of a resulting metal thin film and deteriorating the production yield of the optical devices using the metal thin film.